Ordering number: EN 3471

SANYO No.3471

2SA1433

PNP Epitaxial Planar Silicon Transistor

High-Definition CRT Display Applications

Features

- High f_T (Gain-Bandwidth Product)
- Small reverse transfer capacitance (c_{re} = 1.3pF)
- Adoption of FBET process

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector to Base Voltage	V_{CBO}	−70	V
Collector to Emitter Voltage	V_{CEO}	−60	V
Emitter to Base Voltage	V_{EBO}	−4	V
Collector Current	I_C	−50	mA
Collector Current(Pulse)	I_{CP}	−100	mA
Collector Dissipation	P_C	900	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	−55 to +150	°C

Electrical Characteristics at Ta = 25°C

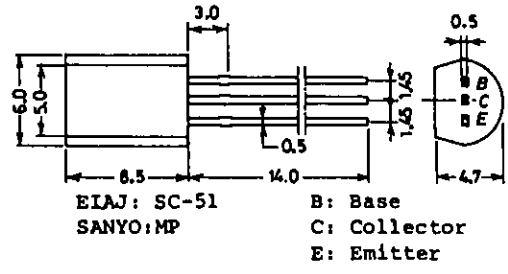
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB} = −40V, I_E = 0			(−)0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB} = −3V, I_C = 0			(−)1.0	μA
DC Current Gain	h_{FE}	V_{CE} = −10V, I_C = −10mA	60*		320*	
Gain-Bandwidth Product	f_T	V_{CE} = −10V, I_C = −10mA	350	700		MHz
Base to Collector Time Constant	$r_{bb}'c_c$	V_{CE} = −10V, I_C = −10mA		8		ps
Output Capacitance	c_{ob}	V_{CB} = −10V, f = 1MHz		1.7		pF
Reverse Transfer Capacitance	c_{re}	V_{CB} = −10V, f = 1MHz		1.3		pF
C-E Saturation Voltage	$V_{CE(sat)}$	I_C = −20mA, I_B = −2mA			−0.6	V
B-E Saturation Voltage	$V_{BE(sat)}$	I_C = −20mA, I_B = −2mA			−1.0	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C = −10μA, I_E = 0	−70			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C = −1mA, R_{BE} = ∞	−60			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_E = −10μA, I_C = 0	−4			V

*: The 2SA1433 is classified by 10mA h_{FE} as follows:

60 D 120	100 E 200	160 F 320

h_{FE} rank : D, E, F

Package Dimensions 2006A
(unit: mm)



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